

S/N 09/652,619

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Gurtej Singh Sandhu et al.

Examiner: Renee Perry

Serial No.: 09/652,619

Group Art Unit: 2818

Filed: August 31, 2000

Docket: 303.085US4

Title: METHOD FOR FORMING A METALLIZATION LAYER

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PATENT
MAIL ROOM
8/6/02AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

Commissioner for Patents
Washington, D.C. 20231

Applicant has reviewed the Office Action mailed on April 26, 2002. Please amend the above-identified patent application as follows.

IN THE CLAIMS

Please substitute the claim set in the appendix entitled Clean Version of Pending Claims for the previously pending claim set. The substitute claim set is intended to reflect cancellation of claim 31, amendment of previously pending claims 21 - 25, 27, 29, 91 and 99, and addition of new claims 100 - 151. The specific amendments to individual claims are detailed in the following marked up set of claims.

21. (Amended) An integrated circuit, comprising:

a substrate;

a first layer of material formed on the substrate, the first layer having contact vias extending through to the substrate, the first layer having a first surface potential;

a second layer formed on the first layer, the second layer lining the contact vias, the second layer being patterned, the second layer having a second surface potential; and

a metallization layer on the second layer, wherein the first layer and the second layer are selected to provide a desired difference between the first surface potential and the second surface potential such that the metallization layer is capable of being selectively electro-deposited on the second layer without being deposited on the first layer using a bipolar modulated voltage.

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01 FC:103 (Amended) The integrated [circuitry] circuit of claim 21, wherein the metallization layer comprises non-alloy copper.

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